

## **Diode - Small Signal**

## MMBD1501A, MMBD1503A, MMBD1504A, MMBD1504A

## **ABSOLUTE MAXIMUM RATINGS**

(Values are at  $T_A = 25^{\circ}C$  unless otherwise noted.) (Notes 1, 2)

Symbol	Pai	Value	Unit	
$V_{RRM}$	Maximum Repetiti	ve Reverse Voltage	200	V
I <sub>F(AV)</sub>	Average Rectified	Average Rectified Forward Current		mA
I <sub>FSM</sub>	Non-Repetitive Peak Forward	Pulse Width = 1.0 s	1.0	Α
	Surge Current	Pulse Width = 1.0 μs	2.0	
T <sub>STG</sub>	Storage Temperature Range		-55 to +150	°C
TJ	Operating Junction	n Temperature	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. These ratings are based on a maximum junction temperature of 150°C.
- These are steady-state limits. onsemi should be consulted on applications involving pulsed or low-duty-cycle operations.

## THERMAL CHARACTERISTICS

(Values are at T<sub>A</sub> = 25°C unless otherwise noted.)

Symbol	Parameter	Value	Unit
P <sub>D</sub>	Power Dissipation	350	mW
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	357	°C/W

## **ELECTRICAL CHARACTERISTICS**

(Values are at T<sub>A</sub> = 25°C unless otherwise noted.)

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>R</sub>	Breakdown Voltage	I <sub>R</sub> = 5.0 μA	200	-	V
V <sub>F</sub>	Forward Voltage	I <sub>F</sub> = 1.0 mA	620	720	mV
		I <sub>F</sub> = 10 mA	720	830	mV
		I <sub>F</sub> = 50 mA	800	890	mV
		I <sub>F</sub> = 100 mA	830	930	mV
		I <sub>F</sub> = 200 mA	0.87	1.10	V
		I <sub>F</sub> = 300 mA	0.90	1.15	V
I <sub>R</sub>	Reverse Current	V <sub>R</sub> = 125 V	_	1.0	nA
		V <sub>R</sub> = 125 V, T <sub>A</sub> = 150°C	_	3.0	μΑ
		V <sub>R</sub> = 180 V	-	10.0	nA
		V <sub>R</sub> = 180 V, T <sub>A</sub> = 150°C	_	5.0	μΑ
C <sub>T</sub>	Total Capacitance	V <sub>R</sub> = 0, f = 1.0 MHz	_	4.0	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

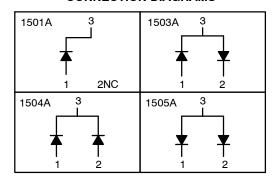






SOT-23 CASE 318BM

#### **CONNECTION DIAGRAMS**



## **MARKING DIAGRAM**



A1x = Specific Device Code

x = 1, 3, 4, 5 M = Date Code

■ = Pb-Free Package

## ORDERING INFORMATION

See detailed ordering and shipping information on page 3 of this data sheet.

## MMBD1501A, MMBD1503A, MMBD1504A, MMBD1505A

### **TYPICAL CHARACTERISTICS**

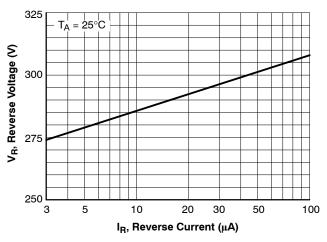


Figure 1. Reverse Voltage vs. Reverse Current  $I_R$  – 3.0 to 100  $\mu A$ 

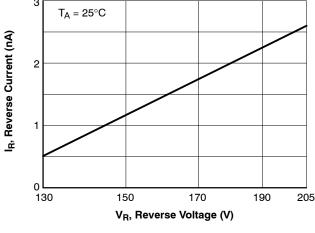


Figure 2. Reverse Current vs. Reverse Voltage V<sub>R</sub> – 130 to 205 V

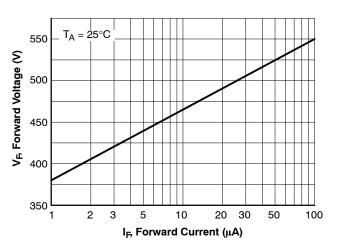


Figure 3. Forward Voltage vs. Forward Current  $I_F$  – 1 to 100  $\mu A$ 

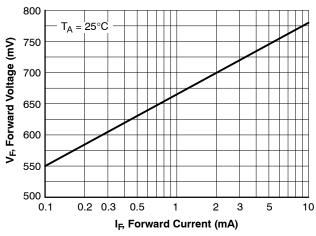


Figure 4. Forward Voltage vs. Forward Current I<sub>F</sub> - 0.1 to 10 mA

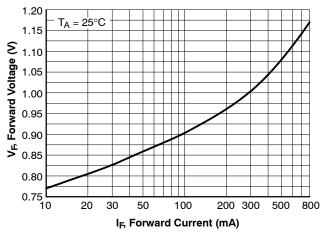


Figure 5. Forward Voltage vs. Forward Current  $I_F - 10$  to 800 mA

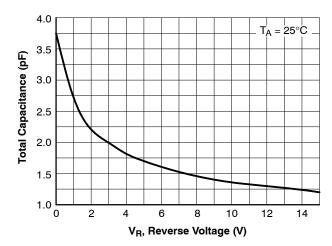


Figure 6. Total Capacitance vs. Reverse Voltage  $V_R$  – 0 to 15 V

## MMBD1501A, MMBD1503A, MMBD1504A, MMBD1505A

## TYPICAL CHARACTERISTICS (Continued)

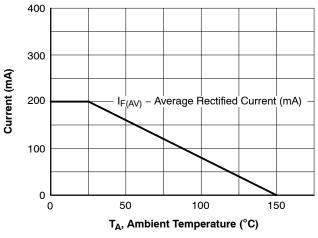


Figure 7. Average Rectified Current ( $I_{F(AV)}$ ) vs. Ambient Temperature ( $T_A$ )

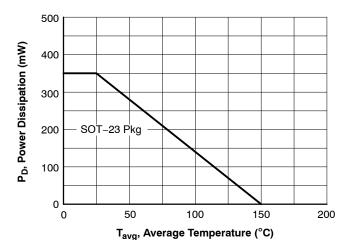


Figure 8. Power Derating Curve

## **ORDERING INFORMATION**

Part Number	Specific Device Marking	Package Type	Shipping <sup>†</sup>
MMBD1501A	A11		
MMBD1503A	A13	1	
MMBD1504A	A14	SOT-23 (TO-236) (Pb-Free)	3,000 / Tape & Reel (7")
MMBD1505A	A15	(1.2.1.55)	
NSVMMBD1504ALT1G*	A16	1	
MMBD1503A_D87Z	A13	SOT-23 (Pb-Free)	10,000 / Tape & Reel (13")
NSVMMBD1501ALT3G*	A11	SOT-23 (TO-236) (Pb-Free)	10,000 / Tape & Reel (13")

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, <a href="https://example.com/BRD8011/D">BRD8011/D</a>.

<sup>\*</sup>NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.



SOT-23 (TO-236) CASE 318-08 **ISSUE AS** 

**DATE 30 JAN 2018** 

# SCALE 4:1 D - 3X b

**TOP VIEW** 







## **RECOMMENDED SOLDERING FOOTPRINT**



DIMENSIONS: MILLIMETERS

#### NOTES:

- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
  MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,

PROT	RUSIONS, OR GATE BURRS.	
		T

	MILLIMETERS		INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°		10°	0°		10°

## **GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code

= Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE
OT (1 F O			

SOT-23 (TO-236)

STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
<ol><li>ANODE</li></ol>	<ol><li>SOURCE</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>CATHODE</li></ol>	2. DRAIN	2. GATE
<ol><li>CATHODE</li></ol>	3. GATE	<ol><li>CATHODE-ANODE</li></ol>	<ol><li>ANODE</li></ol>	3. GATE	<ol><li>ANODE</li></ol>

STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	PIN 1. CATHODE
<ol><li>CATHODE</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>ANODE</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>ANODE</li></ol>	<ol><li>ANODE</li></ol>
<ol><li>ANODE</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>ANODE</li></ol>	<ol><li>CATHODE-ANOD</li></ol>	E 3. GATE

STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
<ol><li>SOURCE</li></ol>	<ol><li>OUTPUT</li></ol>	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3 DRAIN	3 INPLIT	3 CATHODE	3. SOURCE	3. GATE	<ol><li>NO CONNECTION</li></ol>

STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE	
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**DESCRIPTION:** 

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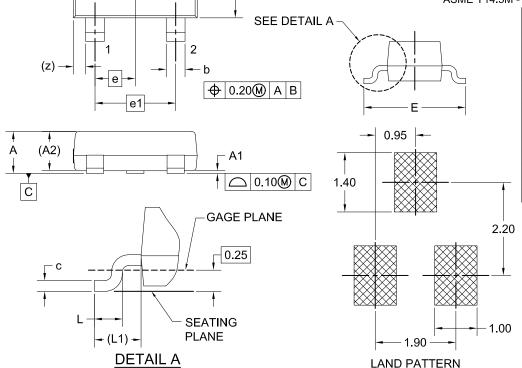


## SOT-23 CASE 318BM ISSUE A

**DATE 01 SEP 2021** 



- A) REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE H.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS ARE INCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.
- D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M 2009.



Α

В

E1

2000.				
DIM	MILLIMETERS			
Diwi	MIN.	NOM.	MAX.	
Α			1.20	
A1	0.00	0.05	0.10	
A2	(	).93 REF		
b	0.37	0.44	0.60	
С	0.08	0.15	0.23	
D	2.72	2.92	3.12	
Е	2.10	2.40	2.70	
E1	1.15	1.30	1.50	
е	0.95 BSC			
e1	1.90 BSC			
L	0.20			
L1	0.55 REF			
Z	(	).29 REF		

GENERIC
MARKING DIAGRAM\*



\*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

RECOMMENDATION

XXX = Specific Device Code
M = Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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